

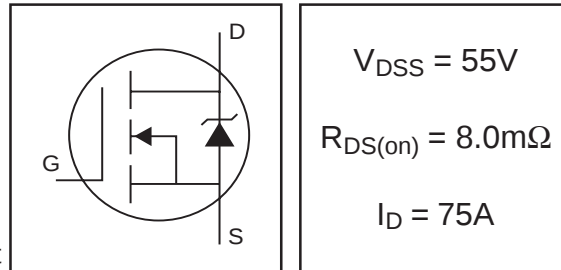
Features

- Logic Level
- Advanced Process Technology
- Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to T_{jmax}

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

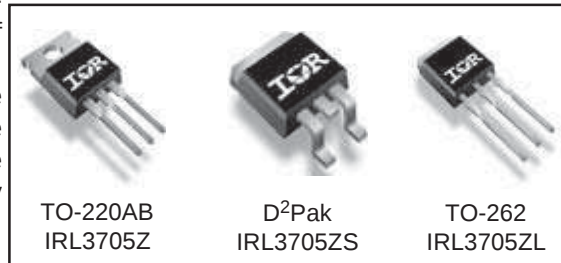
HEXFET® Power MOSFET



$$V_{DS} = 55V$$

$$R_{DS(on)} = 8.0m\Omega$$

$$I_D = 75A$$



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)	86	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	61	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited)	75	
I_{DM}	Pulsed Drain Current ①	340	
$P_D @ T_C = 25^\circ C$	Power Dissipation	130	W
	Linear Derating Factor	0.88	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	120	mJ
E_{AS} (Tested)	Single Pulse Avalanche Energy Tested Value ③	180	
I_{AR}	Avalanche Current ①	See Fig.12a, 12b, 15, 16	A
E_{AR}	Repetitive Avalanche Energy ⑤		mJ
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw ⑦	10 lbf•in (1.1N•m)	

Thermal Resistance

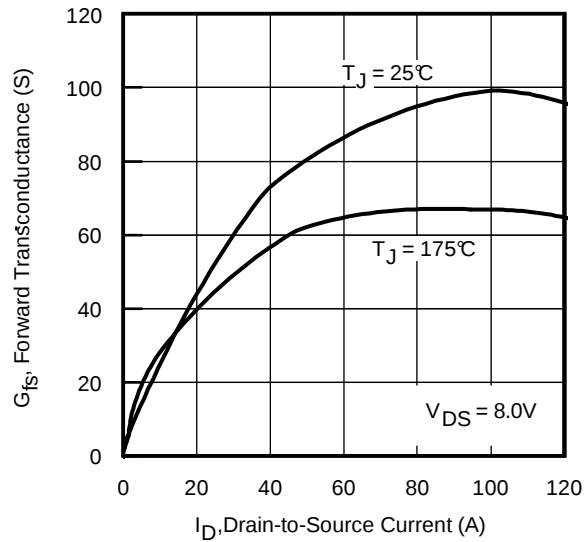
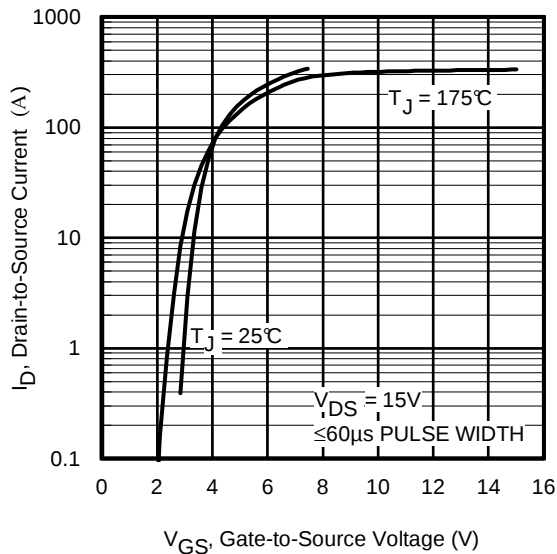
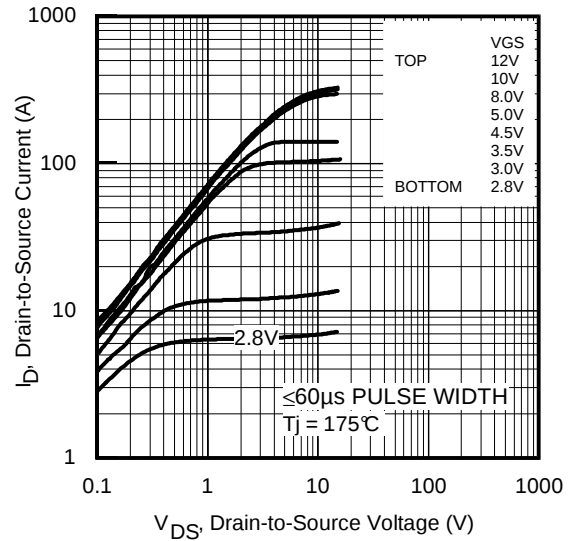
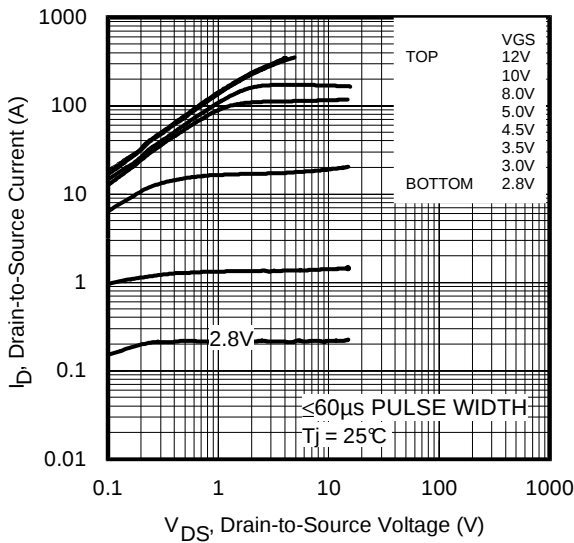
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.14	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface ②	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ②	—	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ③	—	40	

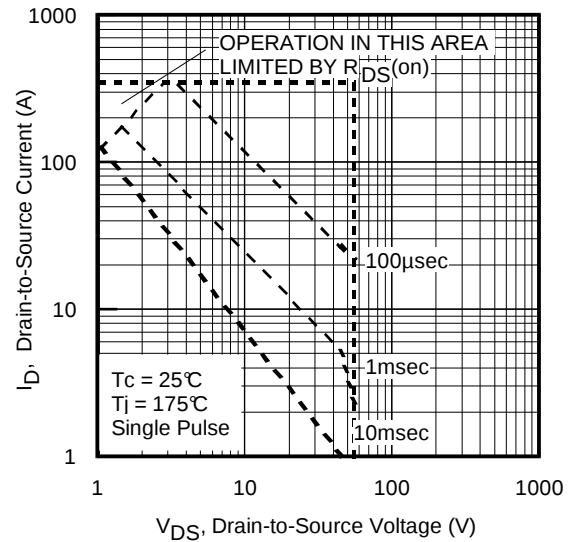
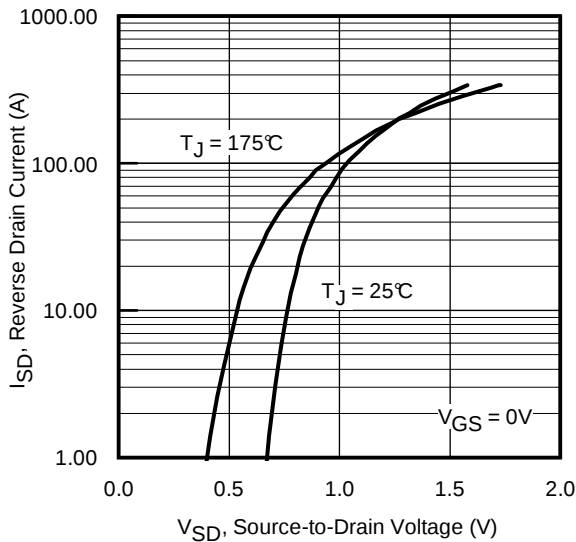
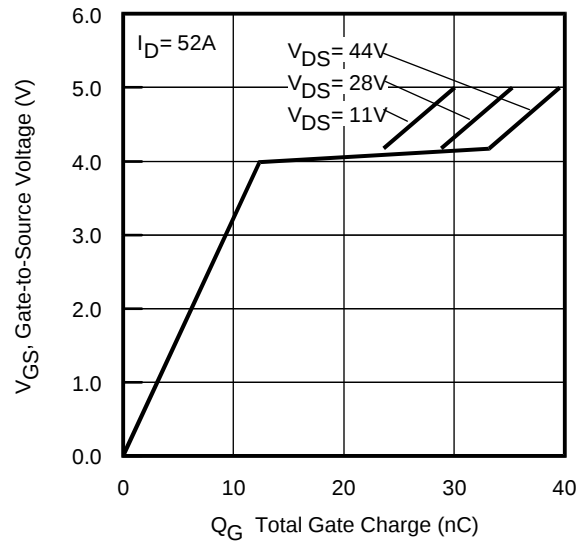
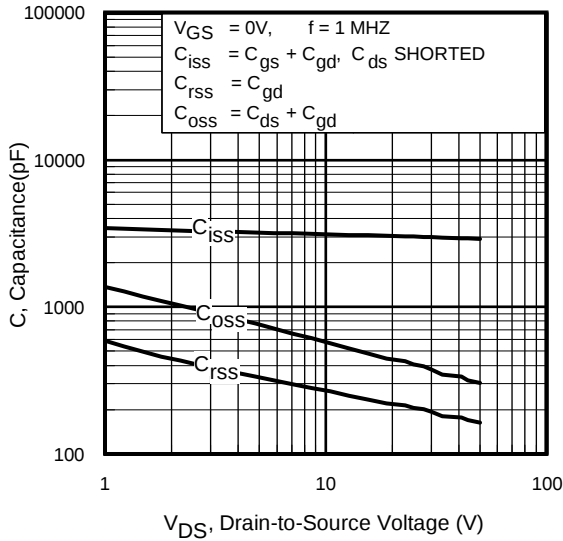
Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

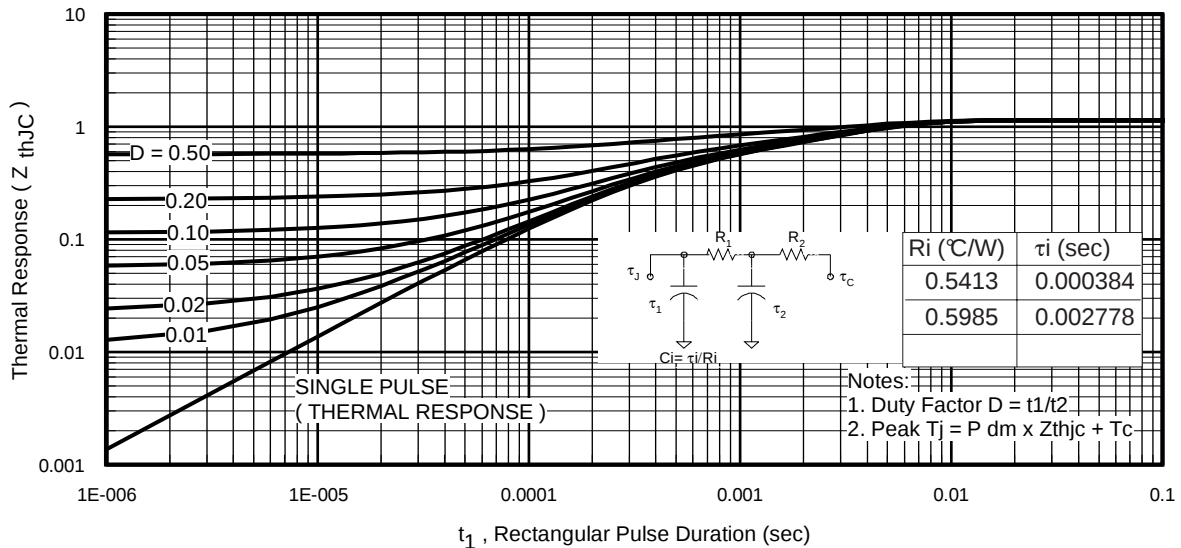
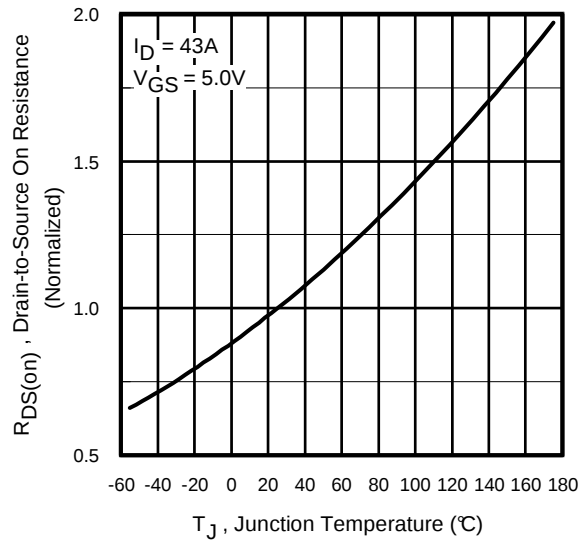
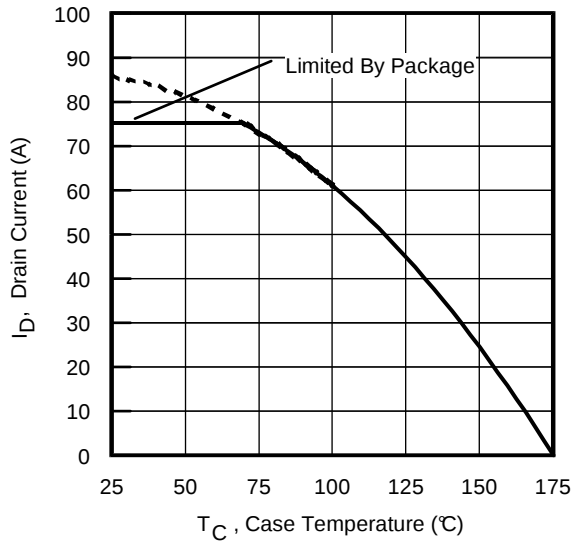
	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.055	—	V/°C	Reference to 25°C , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.5	8.0	m Ω	$V_{GS} = 10V, I_D = 52A$ ③
		—	—	11		$V_{GS} = 5.0V, I_D = 43A$ ③
		—	—	12		$V_{GS} = 4.5V, I_D = 30A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	150	—	—	V	$V_{DS} = 25V, I_D = 52A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 55V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	40	60	nC	$I_D = 43A$
Q_{gs}	Gate-to-Source Charge	—	12	—		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	21	—		$V_{GS} = 5.0V$ ③
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	240	—		$I_D = 43A$
$t_{d(off)}$	Turn-Off Delay Time	—	26	—		$R_G = 4.3 \Omega$
t_f	Fall Time	—	83	—		$V_{GS} = 5.0V$ ③
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	2880	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	420	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	220	—		$f = 1.0MHz$
C_{oss}	Output Capacitance	—	1500	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	330	—		$V_{GS} = 0V, V_{DS} = 44V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	510	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 44V$ ④

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	75	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	340		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 52A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	16	24	ns	$T_J = 25^\circ\text{C}, I_F = 43A, V_{DD} = 28V$
Q_{rr}	Reverse Recovery Charge	—	7.4	11	nC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				







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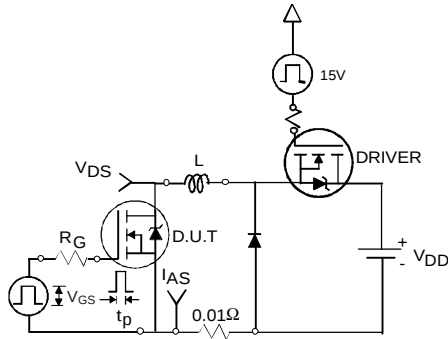


Fig 12a. Unclamped Inductive Test Circuit

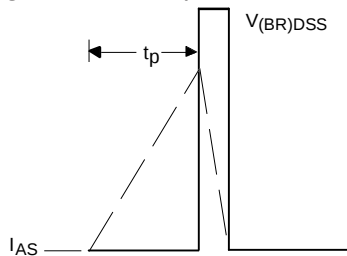


Fig 12b. Unclamped Inductive Waveforms

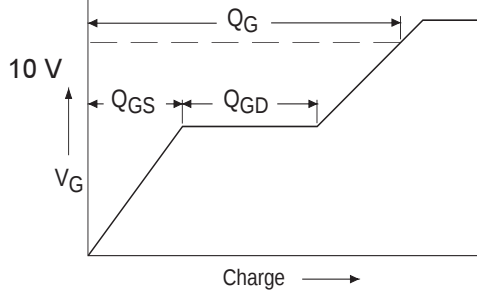


Fig 13a. Basic Gate Charge Waveform

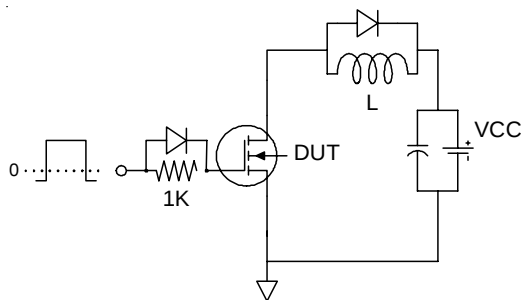


Fig 13b. Gate Charge Test Circuit

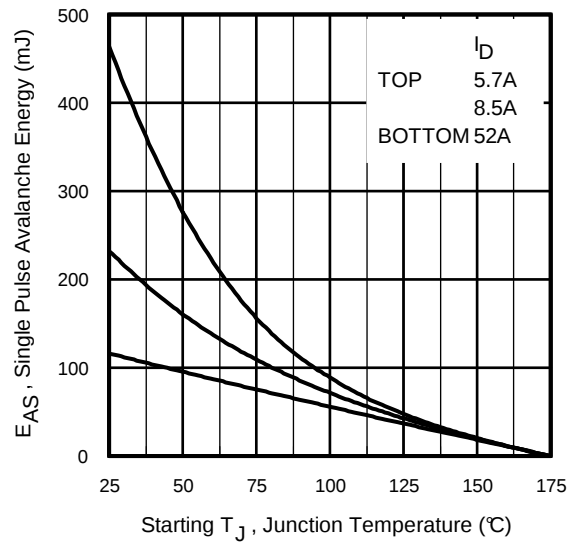


Fig 12c. Maximum Avalanche Energy vs. Drain Current

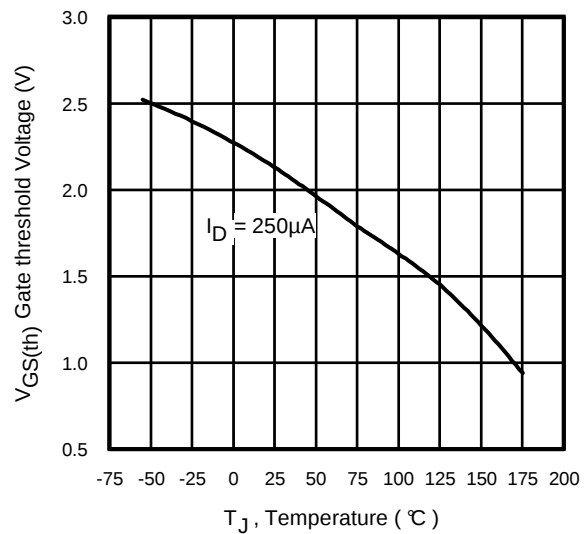


Fig 14. Threshold Voltage vs. Temperature

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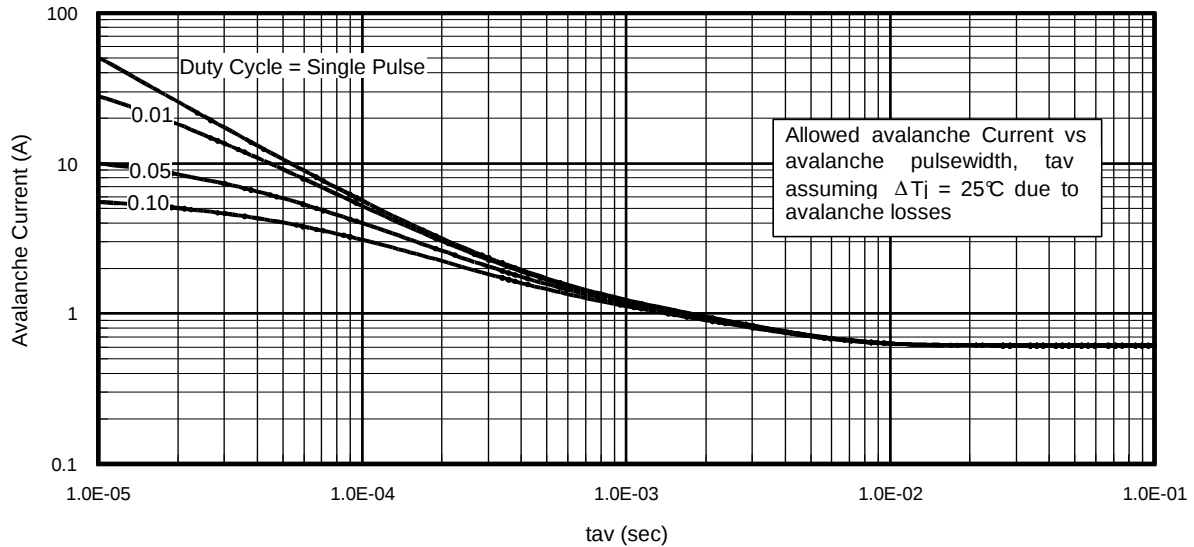


Fig 15. Typical Avalanche Current vs. Pulsewidth

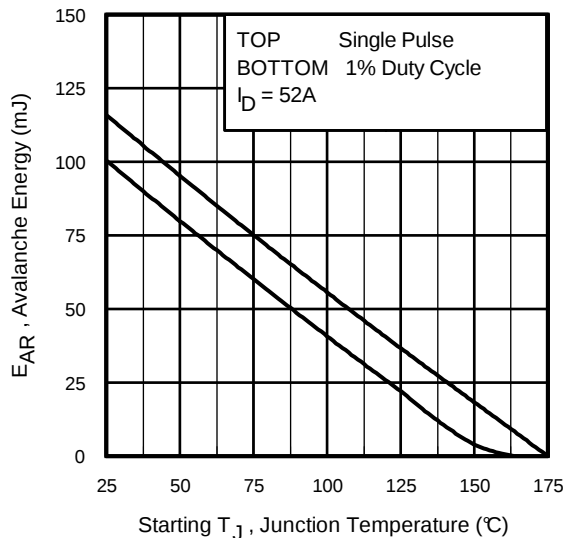


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = \frac{1}{2} (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

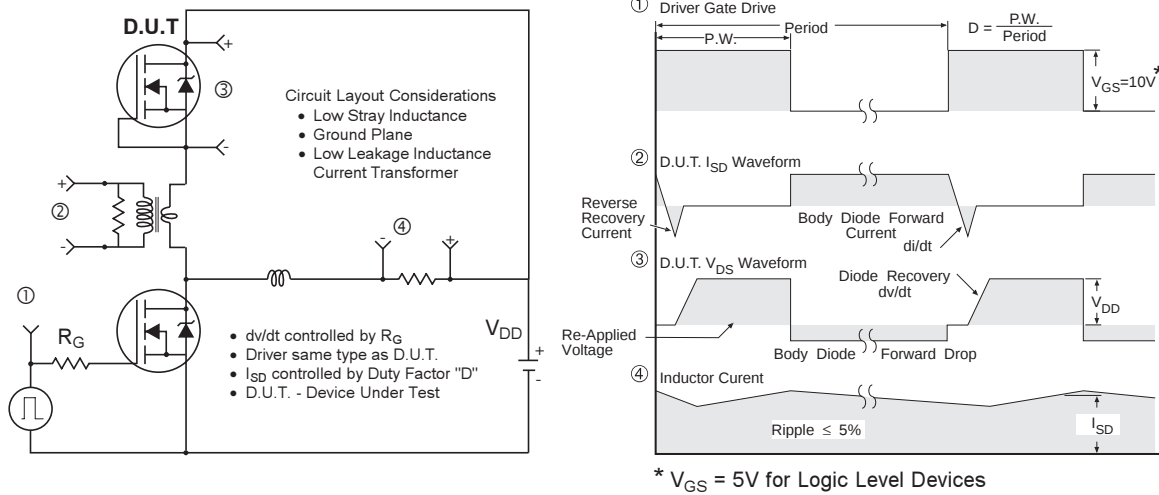


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

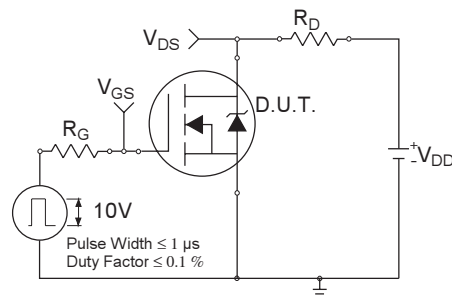


Fig 18a. Switching Time Test Circuit

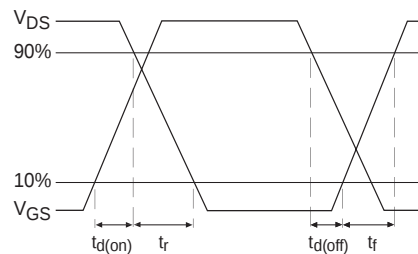
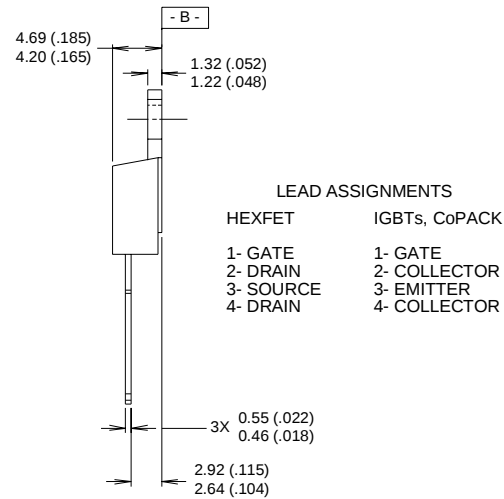
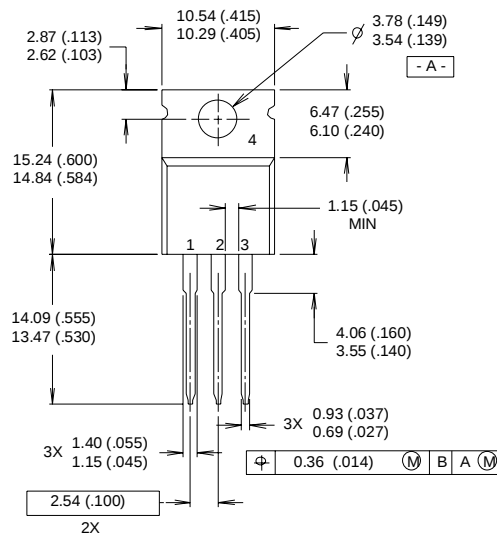


Fig 18b. Switching Time Waveforms

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



LEAD ASSIGNMENTS	
HEXFET	IGBTs, CoPACK
1- GATE	1- GATE
2- DRAIN	2- COLLECTOR
3- SOURCE	3- EMITTER
4- DRAIN	4- COLLECTOR

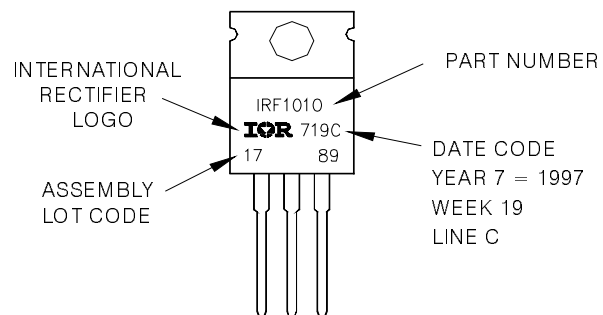
NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"
Note: "P" in assembly line position indicates "Lead-Free"

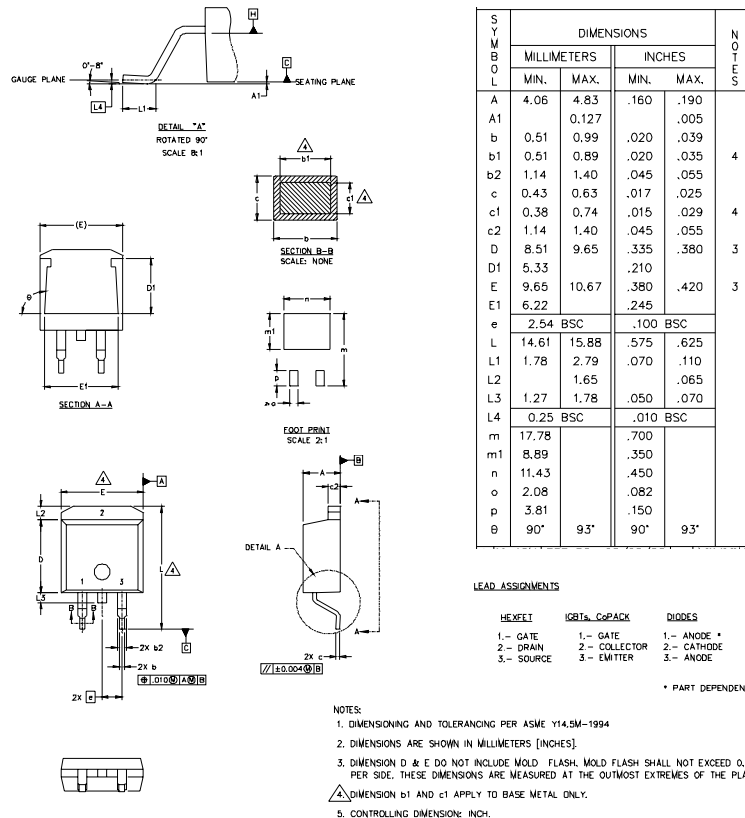


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D²Pak Package Outline

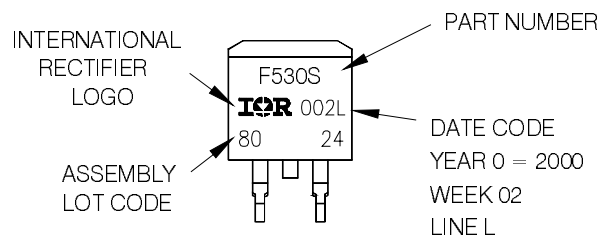
Dimensions are shown in millimeters (inches)



D²Pak Part Marking Information

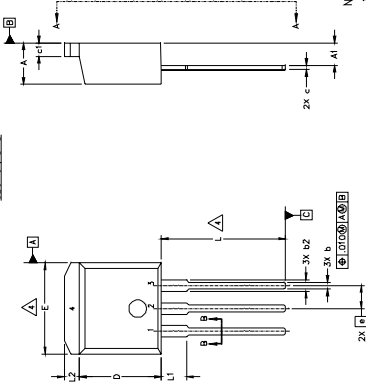
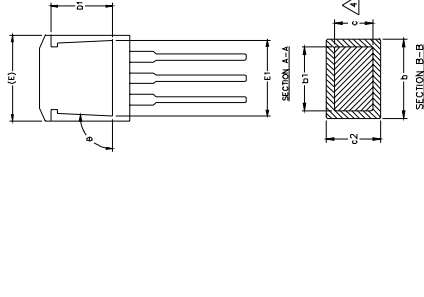
EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"



TO-262 Package Outline

Dimensions are shown in millimeters (inches)

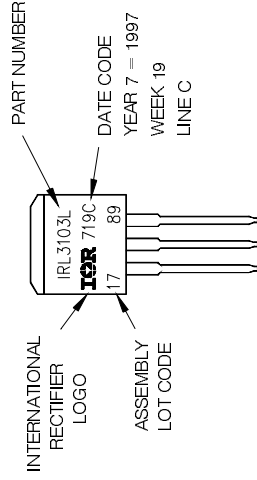


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 5. CONTROLLING DIMENSION: INCH.



TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



IRL3705Z/S/L

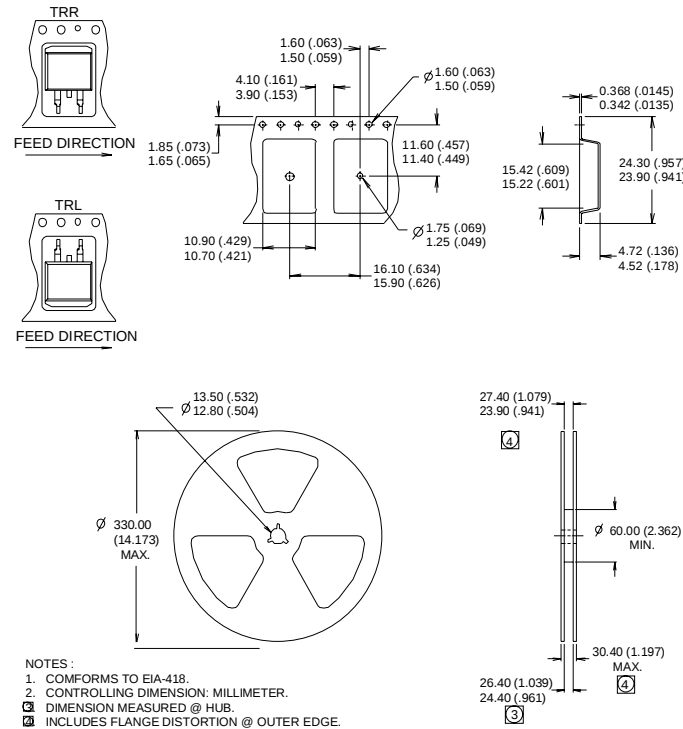
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	3
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33	.210	.210	.420	
E	9.65	10.67	.380	.420	3
E1	6.22	.245	.245	.555	
e	2.54 BSC	.100 BSC	.100 BSC	.555	3
L	13.46	14.09	.530	.146	
L1	3.56	3.71	.140	.065	
L2		1.65			

LEAD ASSIGNMENTS

- HEXFET IGBT
- 1.- GATE 1- GATE
2.- DRAIN 2- COLLECTOR
3.- SOURCE
4.- DRAIN

D²Pak Tape & Reel Information

International
IOR Rectifier



Notes:

- | | |
|--|---|
| ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11). | ⑤ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance. |
| ② Limited by T_{Jmax} , starting $T_J = 25^{\circ}C$, $L = 0.09mH$
$R_G = 25\Omega$, $I_{AS} = 52A$, $V_{GS} = 10V$. Part not recommended for use above this value. | ⑥ This value determined from sample failure population. 100% tested to this value in production. |
| ③ Pulse width $\leq 1.0ms$; duty cycle $\leq 2\%$. | ⑦ This is only applied to TO-220AB package. |
| ④ C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS} . | ⑧ This is applied to D ² Pak, when mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994. |
| | ⑨ R_{θ} is measured at T_J of approximately $90^{\circ}C$. |

TO-220AB package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Automotive [Q101]market.
Qualification Standards can be found on IR's Web site.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

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